## IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for detecting at least one parameter representative of molecular probes fixed to active zones of a sensor, characterized in that wherein said sensor consists of includes a network of field-effect transistors ( $T_1$ ,  $T_2$  etc.), each of which has a source region [[(S)]], a drain region [[(D)]], and a gate region which forms [[a]] one of said active zone (3) zones on which said representative parameter should be is detected, and in that it comprises the method comprising the following steps:

- a) bringing some of said <u>active</u> zones [[(3)]] into contact with molecular probes in order to fix said probes[[,]];
- b) bathing at least these said some of active zones which have been brought into contact with said molecular probes, in [[an]] said electrolyte solution [[(6),]]; and
- c) measuring at least one point of the drain current/source-gate voltage/source-drain voltage at least one of a drain current, source-gate voltage, and source-drain voltage characteristic of at least two of the <u>field-effect</u> transistors of a first group corresponding to zones (3) at least an active zone brought into contact with <u>said</u> molecular probes, so as to deduce therefrom at least one said representative parameter by comparison between at least two measurements obtained for two different <u>active</u> zones <u>immerged</u> in said electrolyte solution.

Claim 2 (Currently Amended): The method as claimed in claim 1, characterized in that wherein said measurement measuring of said at least one point of the characteristic uses the application of comprises:

applying a given voltage (U<sub>DS</sub>) between the drain <u>region</u> and the source <u>region</u> of at least said transistors of the first group and also the application, in a first case, of a given

voltage  $(U_{GS})$  between the gate <u>region</u> and the source <u>region</u> of these transistors of the first group or, in a second case, of a given drain current  $(I_D)$  to these the transistors of the first group.

Claim 3 (Currently Amended): The method as claimed in either of the preceding claims, eharacterized in that it has <u>further comprising</u>: a rinsing step between a) and b).

Claim 4 (Currently Amended): The method as claimed in one of the preceding elaims, characterized in that it comprises claim 1, further comprising, after a) and before b), the following steps:

- a1) rinsing,
- a2) adding a solution containing target molecules capable of interacting specifically with the molecular probes.

Claim 5 (Currently Amended): The method as claimed in one of claims 1 to 6, characterized in that it comprises claim 1, further comprising, after step c), the following steps:

- d) adding an electrolyte solution [[(6)]] containing target molecules capable of interacting specifically with the molecular probes[[,]];
- e) measuring at least one point of the drain current/source-gate voltage/source-drain voltage a drain current, source-gate voltage, and source-drain voltage characteristic of at least two of the transistors of a second group corresponding to said active zones [[(3)]] brought into contact with said molecular probes and with said target molecules, so as to obtain by comparison at least one said representative parameter.

Reply to Office Action of June 19, 2007.

Claim 6 (Currently Amended): The method as claimed in claim 5, characterized in that wherein, in point step e), the measurement of at least one point of the characteristic uses the application of comprises:

applying a given voltage (UDS) between the drain region and the source region of the transistors of at least said two transistors of the second group, and the application applying, in a first case, [[of]] a given voltage (U<sub>GS</sub>) between the gate region and the source region of these the transistors of the second group or, in a second case, of a given drain current (ID) to these the transistors of the second group.

Claim 7 (Currently Amended): The method as claimed in either of claims 5 and 6, characterized in that it uses claim 5, comprising: using a plurality of said measurements of at least one point of the characteristic, which are spaced out over time.

Claim 8 (Currently Amended): The method as claimed in one of the preceding elaims, characterized in that claim 1, wherein said comparison is carried out by differential measurement.

Claim 9 (Currently Amended): The method as claimed in one of the preceding claims, characterized in that claim 1, wherein the comparison is carried out between measurements carried out on at least two transistors corresponding to said active zones [[(3)]] which are bathed in [[an]] said electrolyte solution [[(6)]] after having been brought into contact with said molecular probes.

Claim 10 (Currently Amended): The method as claimed in one of claims 1 to 8, characterized in that claim 1, wherein the comparison is carried out between measurements carried out on at least one transistor corresponding to a <u>first active</u> zone [[(3)]] which is bathed in [[an]] <u>said</u> electrolyte solution [[(6)]] after having been brought into contact with <u>said</u> molecular probes for the purpose of fixing <u>themthe molecular probes</u>, and on at least one transistor corresponding to a <u>second active</u> zone which is bathed in said electrolyte solution [[(6)]] without having been brought into contact with <u>said</u> molecular probes.

Claim 11 (Currently Amended): The method as claimed in one of the preceding elaims, characterized in that claim 1, wherein said representative parameter is a detection of the fixing of the molecular probes to a said zone (3) said one of said active zones.

Claim 12 (Currently Amended): The method as claimed in one of the preceding elaims, characterized in that claim 1, wherein the molecular probes are DNA, RNA or protein molecules.

Claim 13 (Currently Amended): The method as claimed in claim 12, eharacterized in that wherein the molecular probes are DNA molecules and in that the field-effect transistors are of depleted n-channel type, with a negative gate bias.

Claim 14 (Currently Amended): The method as claimed in either of claims 12 and 13, characterized in that it uses claim 12, comprising: using detection by comparison between two zones, each zone comprising at least one said field-effect transistor, the first zone being bathed in a solution obtained from [[an]] a first enzymological reaction (for example, PCR amplification) giving a detectable product specific for the presence or the absence of a mutation in a first DNA sample, and the second zone being bathed in a solution obtained from [[an]] a second enzymological reaction (for example, PCR amplification) giving a DNA

product specific for the presence or for the absence of a mutation in a second DNA sample.

Claim 15 (Currently Amended): The method as claimed in claim 14, eharacterized in that wherein the first and the second DNA samples originate from two patients and in that the first and second enzymological reaction is reactions are the same for the two samples.

Claim 16 (Currently Amended): The method as claimed in claim 14, eharacterized in that wherein the first and the second DNA samples are identical and originate from the same patient, and in that the first enzymological reaction in the first zone is carried out under experimental conditions producing a DNA product in the absence of mutation in the first sample, and in that the second enzymological reaction in the second zone is carried out under experimental conditions producing a DNA product in the presence of a mutation in the second sample.

Claim 17 (Currently Amended): The method as claimed in one of the preceding elaims, characterized in that it comprises the circulation of claim 1, comprising: circulating a solution through at least one microfluid channel, so as to bring [[it]] said solution into contact with at least one said field-effect transistor transistors  $(T_1 ... T_2 etc.)$ .

Claim 18 (New): The method of claim 1, further comprising:

fixing a potential of the electrolyte solution which covers said active zones with a gate electrode immerged in said electrolyte solution.